

## NPN Silicon RF Transistors

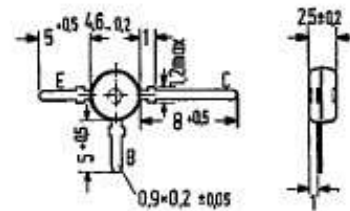
**BF 362**  
**BF 363**

SIEMENS AKTIENGESELLSCHAFT

### for UHF TV tuners

BF 362 and BF 363 are NPN silicon planar RF transistors in a plastic package similar to TO 119 (50 B3 DIN 41867). BF 362 is particularly suitable for gain-controlled input stages, and BF 363 for self-oscillating mixer stages in TV UHF tuners.

Type	Ordering code
BF 362	Q62702-F395
BF 363	Q62702-F396



Approx. weight 0.25 g Dimensions in mm

### Maximum ratings

Collector-emitter voltage  
Collector-base voltage  
Emitter-base voltage  
Collector current  
Junction temperature  
Storage temperature range  
Total power dissipation ( $T_{amb} \leq 55^\circ\text{C}$ )

	BF 362, BF 363	
$V_{CEO}$	20	V
$V_{CBO}$	20	V
$V_{EBO}$	3	V
$I_C$	20	mA
$T_j$	125	$^\circ\text{C}$
$T_{stg}$	-55 to +125	$^\circ\text{C}$
$P_{tot}$	120	mW

### Thermal resistance

Junction to ambient air

$R_{thJA}$	$\leq 680$	K/W
------------	------------	-----

### Static characteristics ( $T_{amb} = 25^\circ\text{C}$ )

Base current  
( $I_E = 3 \text{ mA}$ ;  $V_{CB} = 10 \text{ V}$ )  
Base current  
( $I_E = 12 \text{ mA}$ ;  $V_{CB} = 7 \text{ V}$ )  
Base-emitter forward voltage  
( $I_C = 2 \text{ mA}$ ;  $V_{CE} = 10 \text{ V}$ )

$I_B$	< 150	$\mu\text{A}$
$I_B$	< 1	mA
$V_{BE}$	750	mV

Dynamic characteristics ( $T_{amb} = 25^{\circ}\text{C}$ )		BF 362	BF 363	
Transition frequency ( $I_C = 3 \text{ mA}$ ; $V_{CE} = 10 \text{ V}$ ; $f = 100 \text{ MHz}$ )	$f_T$	800	600-820	MHz
Power gain ( $I_C = 3 \text{ mA}$ ; $V_{CB} = 10 \text{ V}$ ; $f = 900 \text{ MHz}$ ; $R_g = 50 \Omega$ ; $R_L = 500 \Omega$ )	$G_p$	> 11	> 11	dB
Noise figure ( $I_C = 3 \text{ mA}$ ; $V_{CB} = 10 \text{ V}$ ) at $f = 500 \text{ MHz}$ ; $Y_g = 16.7 \text{ mS}$	NF	4	4	dB
at $f = 800 \text{ MHz}$ ; $Y_g = 16.7 \text{ mS}$	NF	4.5	5	dB
Short-circuit reverse transfer capacitance ( $I_C = 1 \text{ mA}$ ; $V_{CE} = 10 \text{ V}$ ; $f = 1 \text{ MHz}$ )	$-C_{12e}$	0.33	0.33	pF
Small-signal short-circuit reverse transfer admittance ( $I_C = 3 \text{ mA}$ ; $V_{CB} = 10 \text{ V}$ ; $f = 900 \text{ MHz}$ )	$ y_{12b} $	0.95	0.95	mS